

#### **Features**

- Low R<sub>DS(on)</sub> & FOM
- · Extremely Low Switching Loss
- · Excellent Stability and Uniformity
- · Fast Switching and Soft Recovery
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Halogen Free. "Green" Device
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1

# **Maximum Ratings**

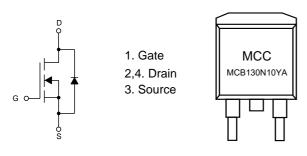
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 60°C/W Junction to Ambient<sup>(1)</sup>
- Thermal Resistance: 0.5°C/W Junction to Case

Parameter	Symbol	Value
Drain-Source Voltage	$V_{DS}$	100V
Gate-Source Volltage	$V_{GS}$	±20V
Continuous Drain Current <sup>(2)</sup> ,T <sub>C</sub> =25°C	I <sub>D</sub>	130A
Pulsed Drain Current <sup>(3)</sup> , T <sub>C</sub> =25°C	I <sub>D,pluse</sub>	440A
Power Dissipation <sup>(4)</sup> , T <sub>C</sub> =25°C	$P_{D}$	260W
Single Pulsed Avalanche Energy <sup>(5)</sup>	E <sub>AS</sub>	900mJ

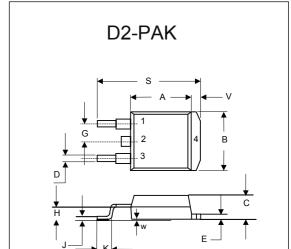
#### Note:

- 1. The Value of  $R_{\theta JA}$  is Measured with the Device Mounted on 1 in<sup>2</sup> FR-4 Board with 2oz. Copper, In a Still Air Environment with  $T_A$ =25°C.
- 2. Calculated Continuous Current Based on Maximum Allowable Junction Temperature.
- 3. Repetitive Rating: Pulse Width Limited By Max. Junction Temperature.
- 4. Pd is Based on Max. Junction Temperature, Using Junction-Case Thermal Resistance.
- 5.  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , L=2mH, Starting  $T_J$ =25 $^{\circ}$ C.

## **Internal Structure and Marking Code**

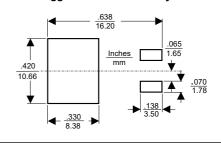


# N-Channel MOSFET



DIMENSIONS						
DIM	INCHES		MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.331	0.370	8.40	9.40		
В	0.378	0.417	9.60	10.60		
С	0.165	0.189	4.20	4.80		
D	0.027	0.037	0.68	0.94		
E	0.045	0.055	1.14	1.40		
G	0.010		2.54		TYP.	
Н	0.096	0.134	2.43	3.40		
J	0.011	0.025	0.28	0.64		
K	0.071	0.131	1.80	3.32		
S	0.575	0.625	14.60	15.87		
V	0.042	0.058	1.07	1.47		
W	0.000	0.010	0.00	0.25		

#### Suggested Solder Pad Layout

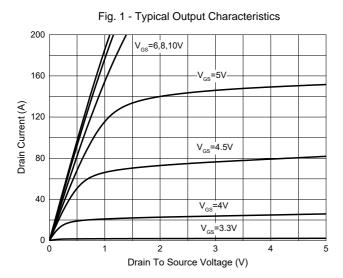


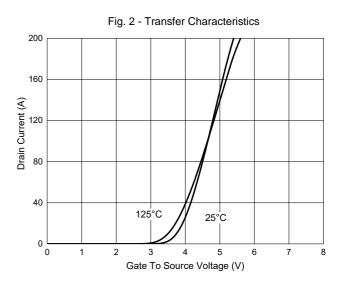


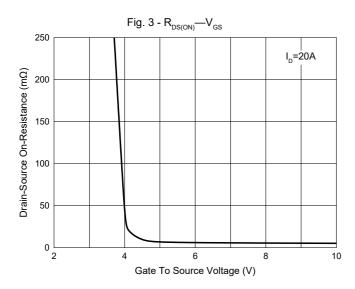
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2	2.8	4	V
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		3.8	4.6	mΩ
Gate Resistance	$R_{G}$	f=1MHz, Open Drain		0.9		Ω
Dynamic Characteristics				•		
Drain-Source On-Voltage	C <sub>iss</sub>			4600		pF
Output Capacitance	C <sub>oss</sub>	$V_{GS}$ =0V, $V_{DS}$ =50V,f=1MHz		1250		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			43		pF
Turn-On Delay Time	t <sub>d(on)</sub>			17.6		ns
Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DS}$ =50V, $R_{G}$ =2.2 $\Omega$ , $I_{D}$ =20 A		30.2		ns
Turn-Off Delay Time	t <sub>d(off)</sub>			33.5		ns
Fall Time	t <sub>f</sub>			39.5		ns
Gate Charge Characteristics						
Total Gate Charge	Qg			66		nC
Gate-Source Charge	Q <sub>gs</sub>	VGS=10V,V <sub>DS</sub> =50V,I <sub>D</sub> =20A		23		nC
Gate-Drain Charge	$Q_{gd}$			6.6		nC
Body Diode Characteristics						
Diode Forward Current	Is	V - N			130	Α
Pulsed Source Current	I <sub>SP</sub>	$V_{GS}$ < $V_{th}$			440	Α
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A, V <sub>GS</sub> =0V			1.3	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =20A,di/dt=100A/µs		63		ns
Reverse Recovery Charge	Q <sub>rr</sub>	15-204,ul/ul-1004/45		93		nC

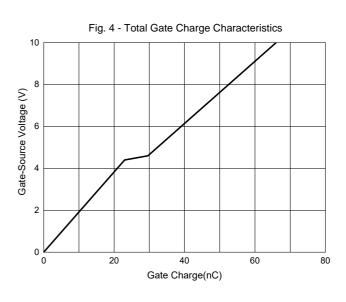


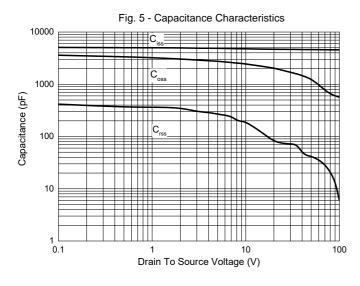
#### **Curve Characteristics**

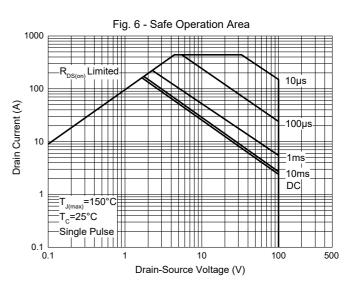














## **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 800pcs/Reel	
Part Number-BP	Tube: 5Kpcs/Ctn	

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